L Number	Hits	Search Text	DB	Time stamp
-	3279	kraft.in.	USPAT;	2004/04/15 07:36
			US-PGPUB;	
			EPO; JPO;	
]			DERWENT;	
!			IBM_TDB	
-	26	kraft.in. and spacers	USPAT;	2004/02/05 18:08
			US-PGPUB;	
			EPO; JPO;	
			DERWENT; IBM TDB	
_	42	kraft.in. and dielectric	USPAT;	2004/02/05 18:24
-	72	Ridit.iii. and dielectric	US-PGPUB;	2004/02/03 10.24
			EPO; JPO;	
		•	DERWENT;	
			IBM TDB	:
-	8	(semiconductor and gate and (spacers same	USPAT;	2004/02/05 18:11
		densi\$7)) and (Xenon or Xe)	US-PGPUB;	
1			EPO; JPO;	·
			DERWENT;	
			IBM_TDB	2004/20/25 12 1
-	1013	semiconductor and gate and (spacers same	USPAT;	2004/02/05 18:14
		densi\$7)	US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
<u>-</u>	823	semiconductor and gate and (spacers same	USPAT;	2004/02/05 18:15
		densi\$7)	EPO; JPO;	,,
i			DERWENT;	
			IBM_TDB	
-	3	(semiconductor) and (spacer with (Xenon or	USPAT;	2004/04/15 07:30
		(Xe))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	5448	(semiconductor) and (spacer with	IBM_TDB USPAT;	2004/02/05 18:27
-	2440	(implant\$3))	US-PGPUB;	2004/02/03 10.2/
		(1	EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3644	(semiconductor) and (spacer with	USPAT	2004/02/05 18:27
		(implant\$3))		0004/00/05 10 55
ļ <del>-</del>	433	<pre>(semiconductor) and (spacer with (implant\$3) with (nitride or SiN or "silicon nitride"))</pre>	USPAT	2004/02/05 18:57
i _	1397		USPAT;	2004/02/05 18:58
-	139/	((438/404) OF (438/218) OF (438/294) OF (438/353)).CCLS.	US-PGPUB;	200-102/02 T0:30
]		. (150, 555) , (600).	EPO; JPO;	
]			DERWENT;	
1			IBM_TDB	
-	20	(((438/404) or (438/218) or (438/294) or	USPAT;	2004/02/05 18:58
		(438/353)).CCLS.) and ((Xe or Xenon or Ge or	US-PGPUB;	
		Germanium) same implant\$3)	EPO; JPO;	
] ]			DERWENT;	
	2-	(seed seed seed) and (seed seed types	IBM_TDB	2004/04/15 07 37
-	35	,	USPAT; US-PGPUB;	2004/04/15 07:37
1		(Xe))	EPO; JPO;	
			DERWENT;	
			IBM TDB	
[ -	226	spacer same (Xenon or Xe)	USPAT;	2004/04/15 07:37
		_	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	
		, , , , , , , , , , , , , , , , , , , ,	IBM_TDB	0004/04/27 27 27
-	11	(spacer same (Xenon or Xe)) and ("integrated	USPAT;	2004/04/15 07:39
1		circuit" or IC)	US-PGPUB; EPO; JPO;	
1			DERWENT;	
			IBM TDB	
L			1 2001 200	

-	3400	spacer with stress	USPAT; US-PGPUB;	2004/04/15 07:39
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	78	(spacer with stress) and (Xenon or Xe)	USPAT;	2004/04/15 07:40
			US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
-	22	((spacer with stress) and (Xenon or Xe)) and	USPAT;	2004/04/15 07:44
		(semiconductor or "integrated circuit" or	US-PGPUB;	
		IC)	EPO; JPO;	
		*	DERWENT;	
f	7914	   semiconductor and (spacer near (film or	<pre>IBM_TDB USPAT;</pre>	2004/04/15 07:45
† <sup>-</sup>	//	layer))	US-PGPUB;	2001/01/13 07:13
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	48	(semiconductor and (spacer near (film or	USPAT;	2004/04/15 14:17
1		layer))) and ((germanium or Ge or xenon or Xe) near (ion or atom))	US-PGPUB; EPO; JPO;	
		Act hear (1011 of acom)	DERWENT;	
			IBM TDB	
-	49128	(selectiv\$3 or etch\$3) with (nitride or SiN)	.USPAT;	2004/04/15 14:19
		·	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	624	(selectiv\$3 or etch\$3) with (nitride or SiN)	USPAT;	2004/04/15 14:22
		same (Xe or Ge or Xenon or Germanium)	US-PGPUB;	, , , , , , , , , , , , , , , , , , , ,
			EPO; JPO;	
			DERWENT;	·
	70	(selectiv\$3 near etch\$3) with (nitride or	<pre>IBM_TDB USPAT;</pre>	2004/04/15 14:36
-	/0	SiN) same (Xe or Ge or Xenon or Germanium)	US-PGPUB;	2004/04/15 14:36
		5211, 54110 (115 01 05 02 11011011 01 001111111111)	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	1088	(selectiv\$3 near etch\$3) with (nitride or SiN) same (ion or atom)	USPAT; US-PGPUB;	2004/04/15 14:36
		SIN/ Same (Ton Of acom)	EPO; JPO;	
	1		DERWENT;	
			IBM_TDB	
-	58	(selectiv\$3 near etch\$3) with (nitride or	USPAT;	2004/04/15 15:44
		SiN) same ((ion or atom) with (implant\$3))	US-PGPUB;	
1		same spacer	EPO; JPO; DERWENT;	
			IBM TDB	
-	17	(("4818714") or ("5597751") or ("5714412")	USPAT	2004/04/15 15:48
		or ("5766988") or ("5789296") or ("5811853")		
		or ("5858840") or ("5872036") or ("5909622")		
		or ("5970371") or ("6001690") or ("6031264") or ("6140182") or ("6165845") or ("6166405")		
		or ("6184088") or ("6187657")).PN.		
-	333	(selectiv\$3 near etch\$3) with (nitride or	USPAT;	2004/04/15 16:05
		SiN) same ((ion or atom) with (implant\$3))	US-PGPUB;	
			EPO; JPO;	]
			DERWENT; IBM TDB	
-	87	spacer with (Ge or germanium) and (gate near	USPAT;	2004/06/11 14:52
		electrode)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
_	522	(germanium or Ge) near (implant\$3)	<pre>IBM_TDB USPAT;</pre>	2004/06/11 14:52
1	522	. (Sermanitum of Se) hear (Implantes)	US-PGPUB;	1001,00,11 14.32
			EPO; JPO;	
1			DERWENT;	
	1		IBM_TDB	L

_	36	((germanium or Ge) near (implant\$3)) same	USPAT; 2004/06/11	14:53
		(spacer or spacers)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	13	((germanium or Ge) near (implant\$3)) with	USPAT; 2004/06/11	14:57
		(spacer or spacers)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	((Xenon or Xe) near (implant\$3)) with	USPAT; 2004/06/11	14:57
ľ		(spacer or spacers)	US-PGPUB;	
	İ	(Spacer or Spacers)	EPO; JPO;	
			DERWENT;	
		*	IBM TDB	
1 _	5	((Xenon or Xe) near (implant\$3)) same	USPAT; 2004/06/11	15.16
-	3	(spacer or spacers)	US-PGPUB;	15:10
		(spacer or spacers)	EPO; JPO;	
Ì				
1			DERWENT;	
	740	(implant (2) many (many on many)	IBM_TDB	15 10
-	742	(implant\$3) near (spacer or spacers)	USPAT; 2004/06/11	15:18
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	439	(implant\$3) near (spacer or spacers) and	USPAT; 2004/06/11	15:18
		semiconductor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	29	("4060427"   "4102733"   "4272880"	USPAT 2004/06/11	15:59
		"4298629"   "4330931"   "4382827"		
		"4402761"   "4455742"   "4512074"		
		"4542580"   "4589936"   "4621277"		
		"4623912"   "4629520"   "4715937"		
		"4775642"   "4835112"   "5093700"		
		"5168072"   "5180690"   "5266514"		
		"5276347"   "5326722"   "5600166"		
		"5683929"   "5792690"   "5915182"		
		"5969397"   "6015740").PN.		
-	1	6331468.URPN.	USPAT 2004/06/11	16:02
L	·		1	